

IN THE CLAIMS

Please cancel claims 2, 5, and 9, without prejudice or disclaimer.

Please amend claims 1 and 7 as follows:

C1 SUB D1
1. (Thrice Amended) A method for forming a first-property semiconductor film at a desired position on a substrate, comprising the steps of:

- a) preparing the substrate having a second-property semiconductor film formed thereon, wherein the substrate has an alignment mark previously formed thereon;
- b) preparing an optical mask having a predetermined pattern on another substrate which is apart from the substrate;
- c) relatively positioning a projection area of the optical mask at the desired position on the substrate by using the alignment mark as a reference;
- d) irradiating the desired position of the second-property semiconductor film with laser light through the optical mask to change an irradiated portion of the second-property semiconductor film to the first-property semiconductor film; and
- e) forming an insulation film on the first-property semiconductor film and the second-property semiconductor film.

C2
7. (Thrice Amended) A method for forming a crystalline semiconductor film at a desired position on a substrate, comprising the steps of:

- a) preparing the substrate having an amorphous semiconductor film formed thereon, wherein the substrate has an alignment mark previously formed thereon;
- b) preparing an optical mask having a predetermined pattern on another substrate which is apart from the substrate;

Cont
C2

- c) relatively positioning a projection area of the optical mask at the desired position on the substrate by using the alignment mark as a reference;
- d) irradiating the desired position of the amorphous semiconductor film with laser light through the optical mask to change an irradiated portion of the amorphous semiconductor film to the crystalline semiconductor film; and
- e) forming an insulation film on the crystalline semiconductor film and the amorphous semiconductor film.

REMARKS

Applicant has rewritten claims 1 and 7, and cancelled claims 2, 5 and 9, without prejudice or disclaimer.

DOUBLE PATENTING REJECTION

Claim 5 is objected to under 37 C.F.R. § 1.75 as being substantially duplicative of claim 7. Applicant cancels claim 5 without prejudice or disclaimer, and respectfully requests that this objection be withdrawn.

CLAIM REJECTION UNDER 35 U.S.C. § 103(a)

Claims 1-10 are rejected under 35 U.S.C. §103(a) as being unpatentable over "Single-crystal Si films for thin-film transistor devices" to Im et al. in view of U.S. Patent No. 5,492,843 to Adachi et al. Applicant cancels claims 2, 5, and 9, without prejudice or